



Двойной слой и адсорбция на идеально поляризуемых электродах - самая длинная история школы А.Н.Фрумкина

(1934)

2 :

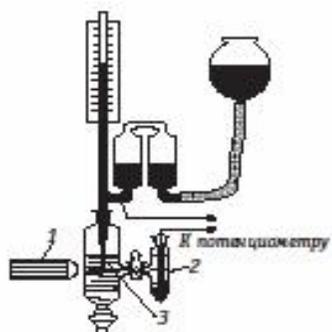
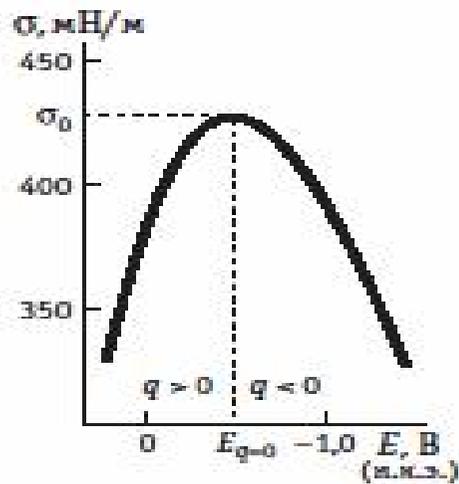


Рис. 7.6. Упрощенная схема капиллярного электрометра Гум: 1 — горизонтальный микроскоп; 2 — каломельный электрод; 3 — конический капилляр



$q, E - C, E -$

$$C = \left(\frac{\partial q}{\partial E} \right)_{A_1} = - \left(\frac{\partial^2 \sigma}{\partial E^2} \right)_{A_1}$$

Hg- 0,5

Na₂SO₄

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(1916-1922)

• 1915 . . .



1916

- 3. . . . // . . . 1916. . . .
48, 8/9. . 1959.
- 4. . . . // . . . 1916. . 48,
8/9. . 1959–1960.

1917

- 5. . . . // . . .
. . . 1917. . 49, 3/4. . 207–210

1919

- . . . «
- » . . . , 280 .

1920

- 6. *Frumkin A. On the theory of electrocapillarity. I // Philos. Mag. 1920. Vol. 40, N 237. . . . 363–375.*
- 7. *Frumkin A. On the theory of electrocapillarity. II // Philos. Mag. 1920. Vol. 40, N 237. P. 375–385.*

1921

- 8. *Frumkin A. Zur Theorie der Adsorption // -
. . . 1921. . 1, 1. . 36–48.*

А. Н. Фрумкинъ.

ЭЛЕКТРОКАПИЛЛЯРНЫЯ ЯВЛЕНІЯ

ЭЛЕКТРОДНЫЯ ПОТЕНЦІАЛЫ.



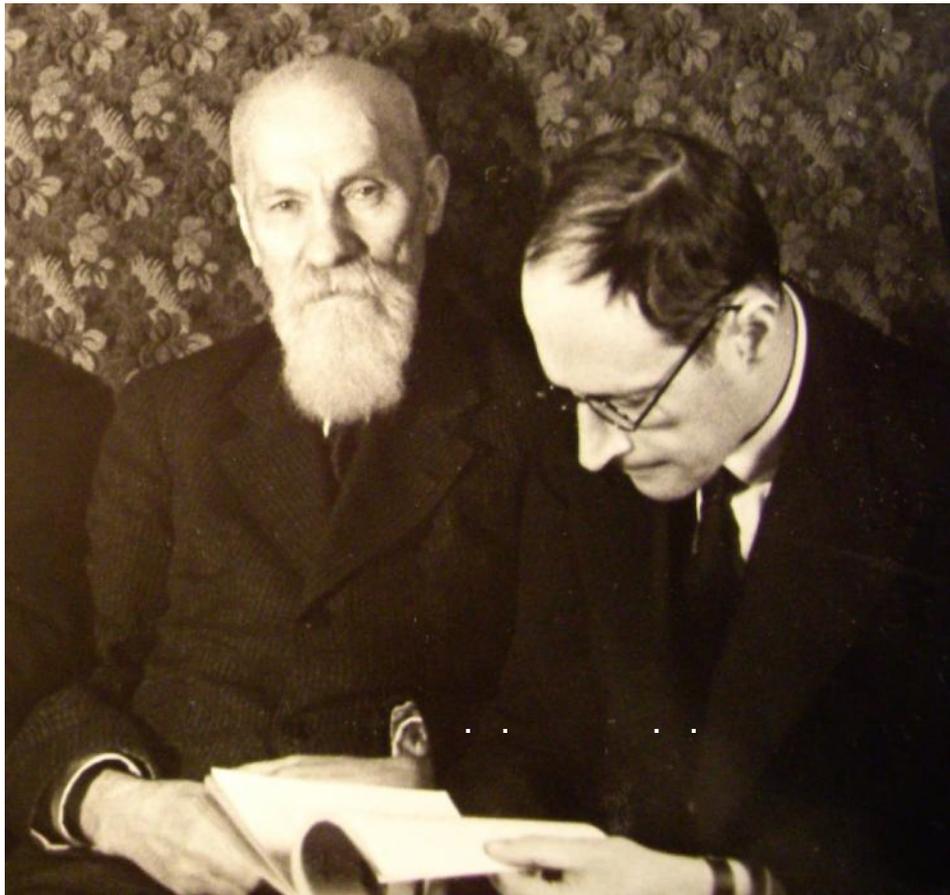
ОДЕССА.

«Киевская полиграф.» В. И. Савицкий, Жукетскы, 12.

1919

(1922-1932 .)

1922 -



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-Hg/ ,
- / .

Механизмы процессов адсорбции на твердой поверхности. Основной объект исследований – активированный уголь. Взаимосвязь поверхностных и электрохимических свойств металлов; условия возникновения разности потенциалов на границе металл/раствор.

90%

1922-1932 .

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• 1933 .

1976

• 1933 . .

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• 1934 .

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« » (1 1.1.1934 .)

1934 .– 1948 .–
(1949 .),

1947 .

-Lewina S., Frumkin A., Lunev A. *Der Einfluss von Platin auf die Adsorptionseigenschaften der Kohle in Elektrolytlosungen* // Acta physicochim. URSS. 1935. Vol.3. N4. S.397-412.

” // ” . 1936. .7, 5. .664-673.

•

- . 12. 5. . 541. // . 1938.

- . . *Change in the drop of potential at the air solution interface as related to the age of the latter.* . 1939. . 24. . 149–151.

- **Frumkin A., Pankratov A.** *Properties of monomolecular layers on solutions of salts. II* // *Acta physicochim. URSS.* 1939. Vol.10. N1. P.55-64.

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1937 . – , , - : -
(1966 .), “ ”.

• 1939 . . .

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1945 .

• 1958 . . .

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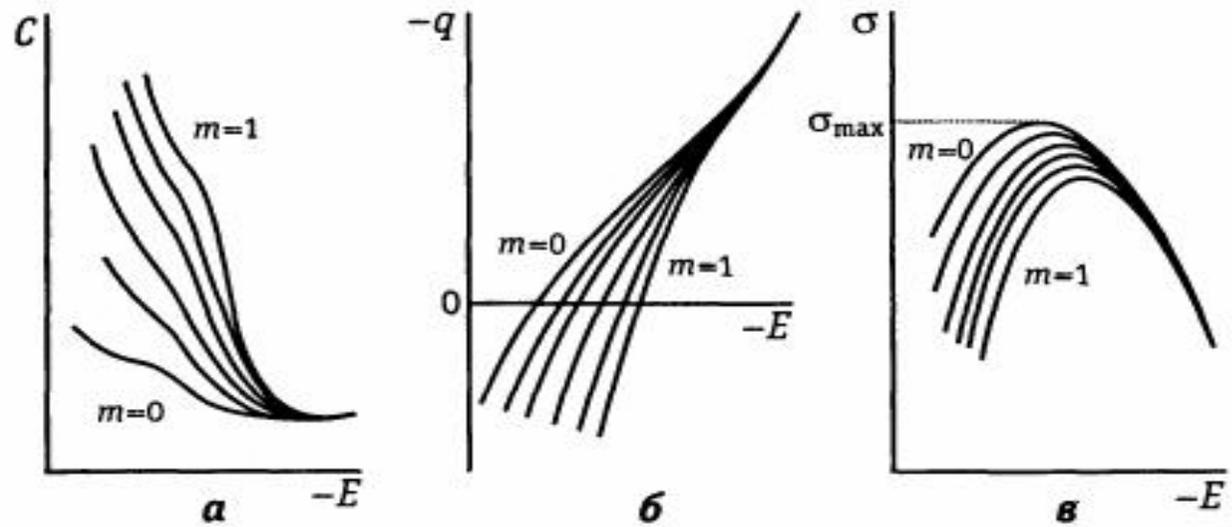


Рис. 7.15. Характерные кривые емкости (а), кривые заряда (б) и электрокапиллярные кривые (в) для системы m с M NaI + (1 - m)с M NaF

Hg/

- M. Proskurnin, A. Frumkin , Trans. Faraday Soc. 36(1935) 110.
- . . . , . . . 24 (1939) 918.
- . . . , . . . 24 (1939) 915.
- . . . , (1940) 3.
- A. Frumkin Trans. Faraday Soc. 36 (1940) 117.

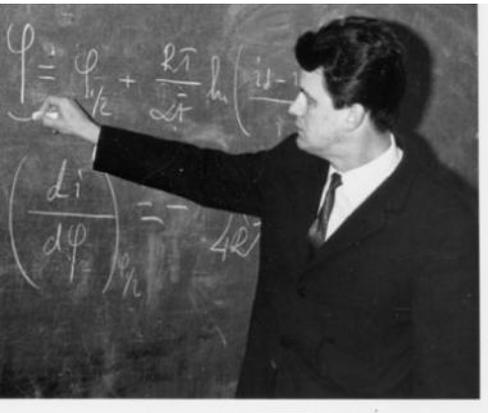
1948. .22. .925.

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Hg-
Hg/



Hg-

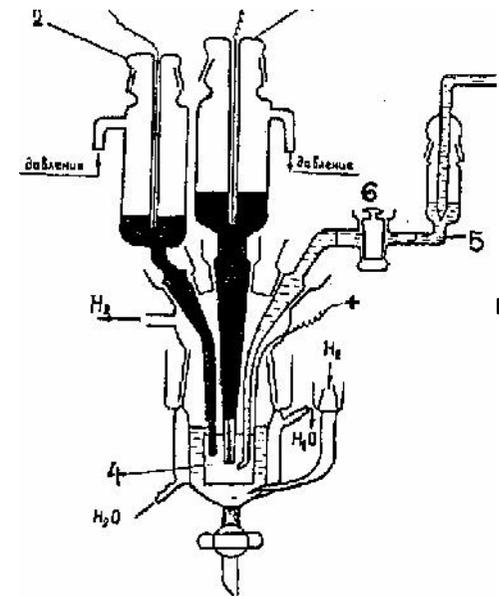
Hg-

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Hg -

1968

Hg-

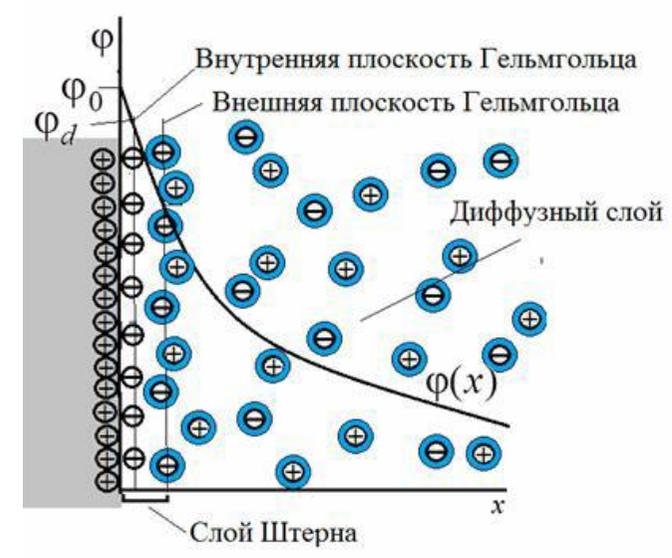
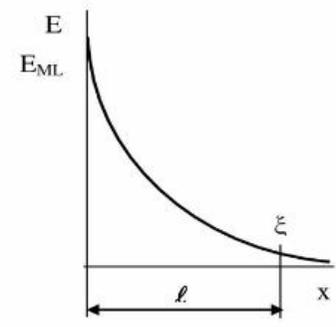
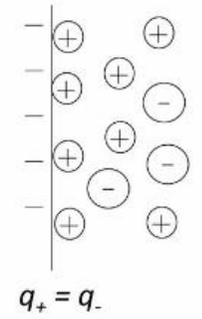
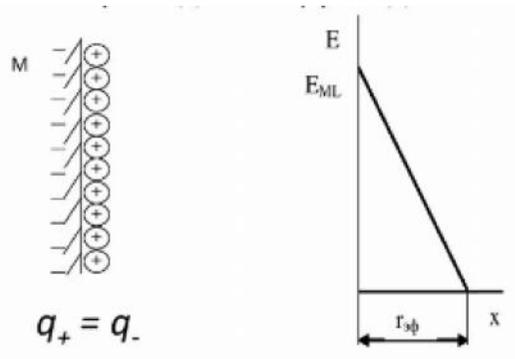


60-



Научный руководитель лаборатории электрохимии проф. У. В. Пальм и зав. каф. неорганической химии проф. В. Э. Паст — ведущие специалисты по изучению кинетики электродных процессов.

Bi -



1879

- 1910 .
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1924 . .

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1947

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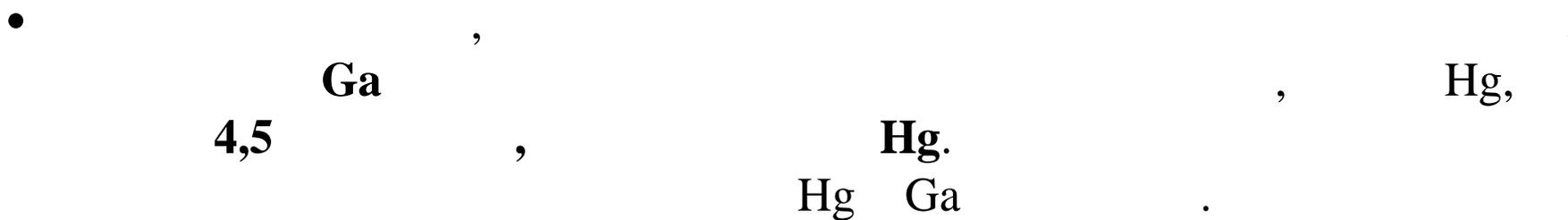
Ga-



. 1964. .157. .957.



- Frumkin A., Polianovskaya N., Grigoryev N., Bagotskaya I. Electrocapillary phenomena on gallium. // Electrochim. Acta. 1965. V.10. P.793.



(1921 – 2007)

4,5

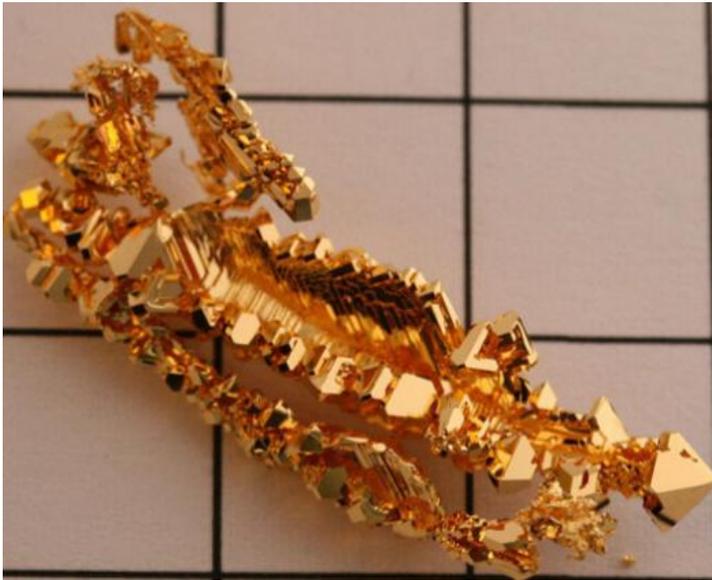
Hg.

Hg Ga



Hg

Ga



1957 .

Pb

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1979

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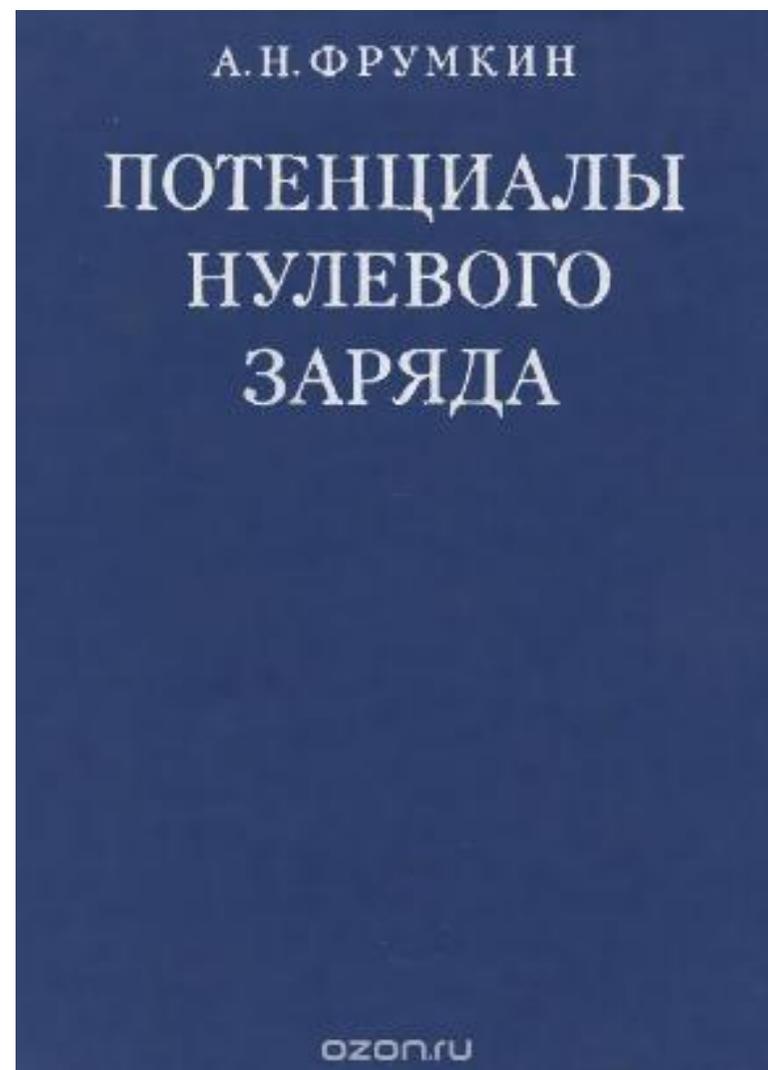
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**(Pb-Sn), (Sb-Pb), (Sb-Sn), (Ag-Sn), (Au-Sn),
(Au-Ag), (Ag-Cd) (Ag-Bi)**
• • , • •

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Al

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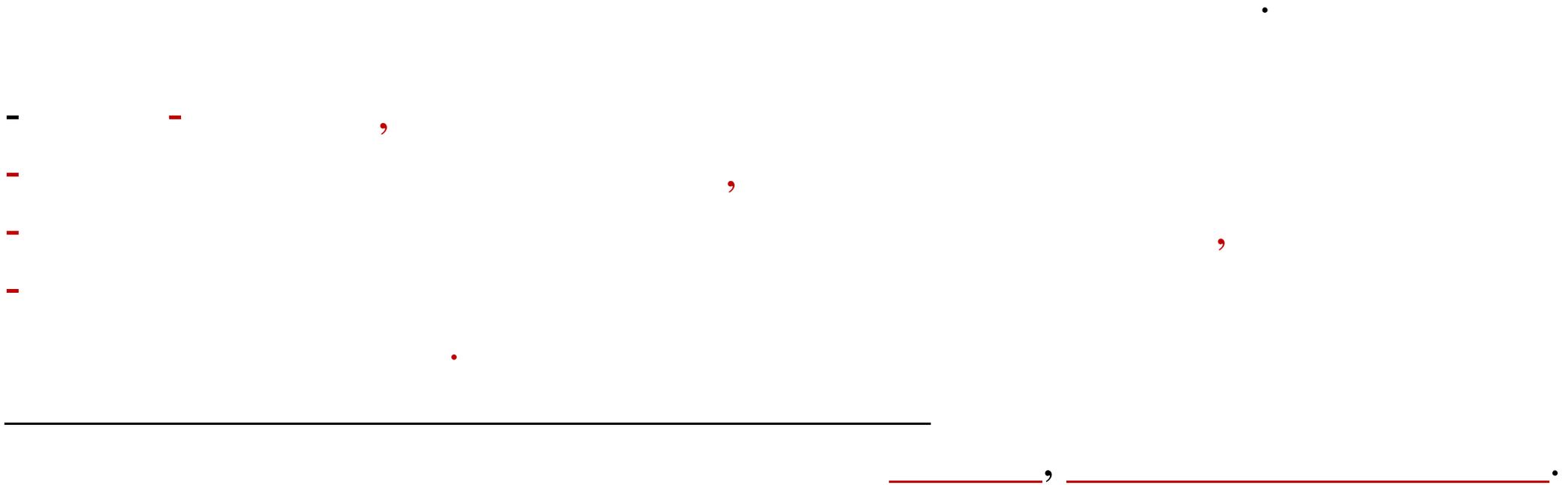
Hg -
• • , • • ,
• • , • •
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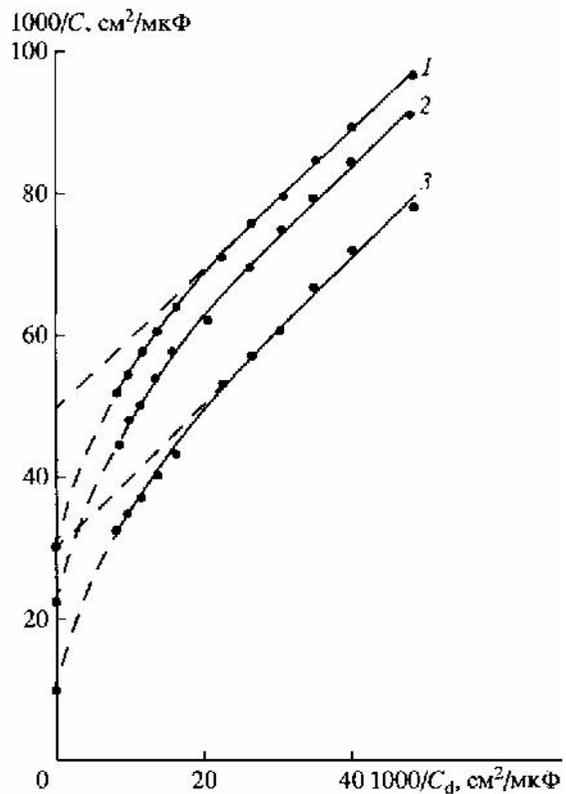
•
Hg, Ga, (In-Ga), (Tl-Ga), (Hg-Ga), (Bi-Ga),
(Sn-Ga), (Pb-Ga), (Cd-Ga)
• • , • • , • •
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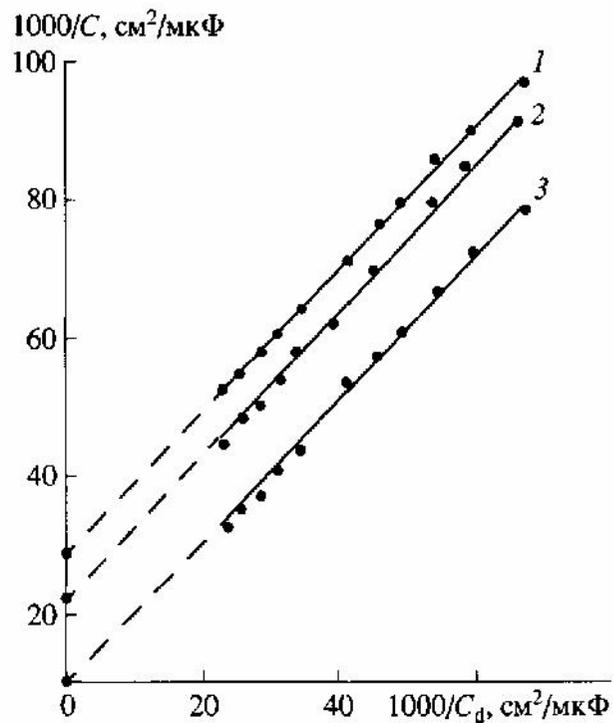
: Hg, Ga, (In-Ga),
(Tl-Ga), (Hg-Ga), (Bi-Ga), (Sn-Ga), (Pb-Ga), (Cd-Ga)

Hg, Bi, Sn, Pb **Cd** **Ga** **: In, Tl,**
In, Tl, Hg, Bi, Sn, Pb **Cd.**

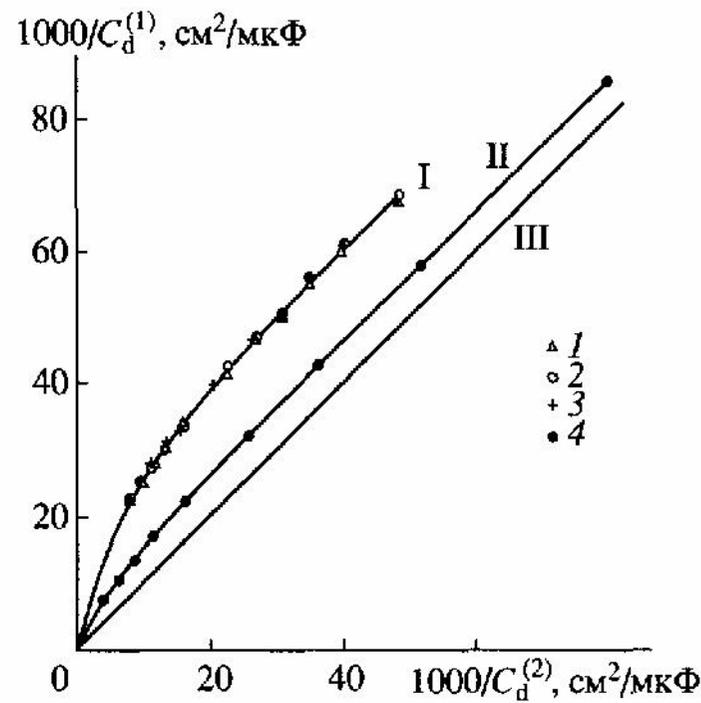




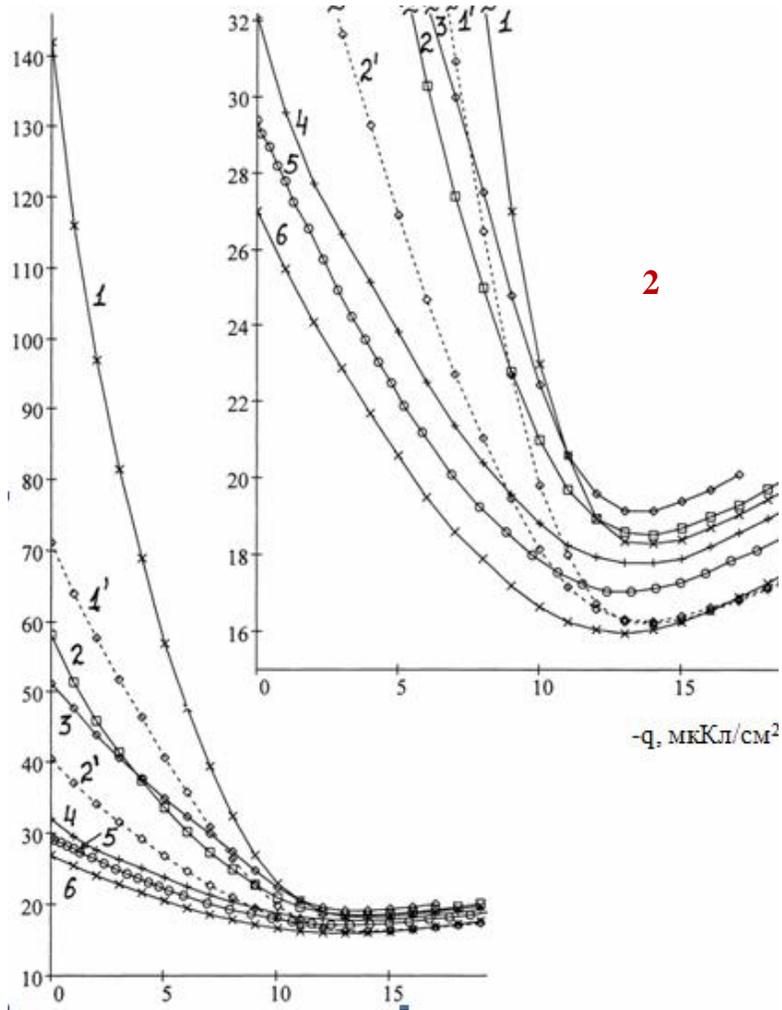
1 - Hg-, 2 - Tl-Ga- 3 -
Cd-Ga-
La₂(SO₄)₃ 32° .
C_d



1 - Hg-, 2 - Tl-Ga- 3 -
Cd-Ga-
La₂(SO₄)₃ 32° .
d .1



I - La₂(SO₄)₃; II -
Na₂SO₄. 1-3 - La₂(SO₄)₃ Hg (1),
Tl-Ga (2) Cd-Ga (3), 4 -
Na₂SO₄ Cd-Ga. III -



$q \approx 0.5$

Na_2SO_4 : 1 – Ga, 2 – In–Ga, 3 – Cd–Ga,
 4 – Tl–Ga, 5 – Tl–Ga, 6 – Hg; C^{chem}, q :
 1' – Ga, 2' – In–Ga.

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• 2

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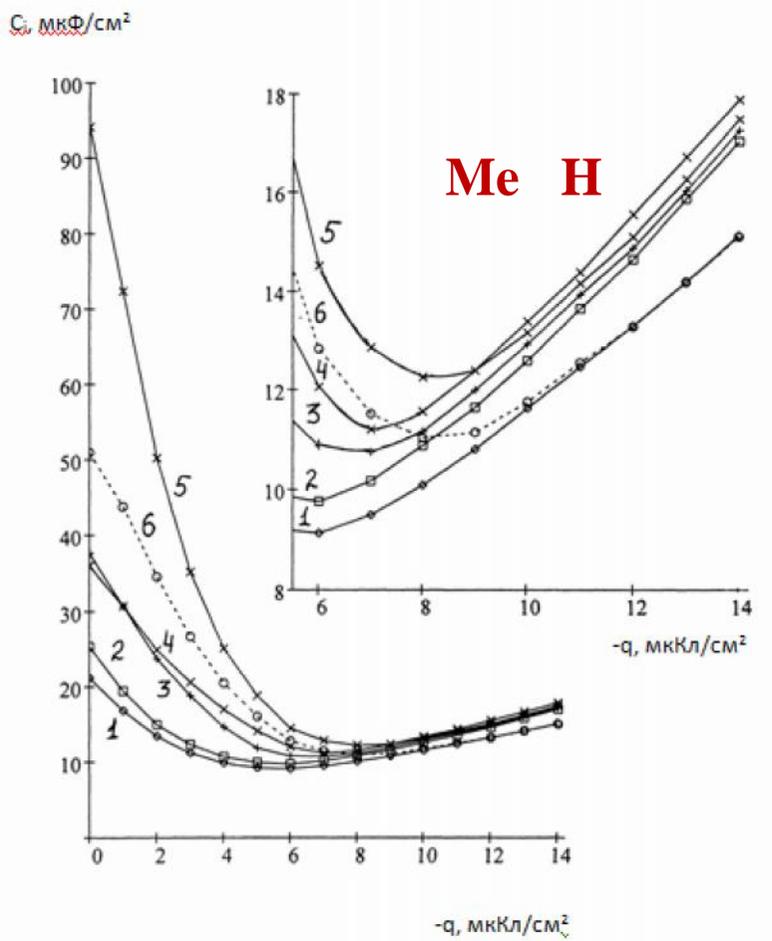
$q \ll 0.$

$q=0,$

:

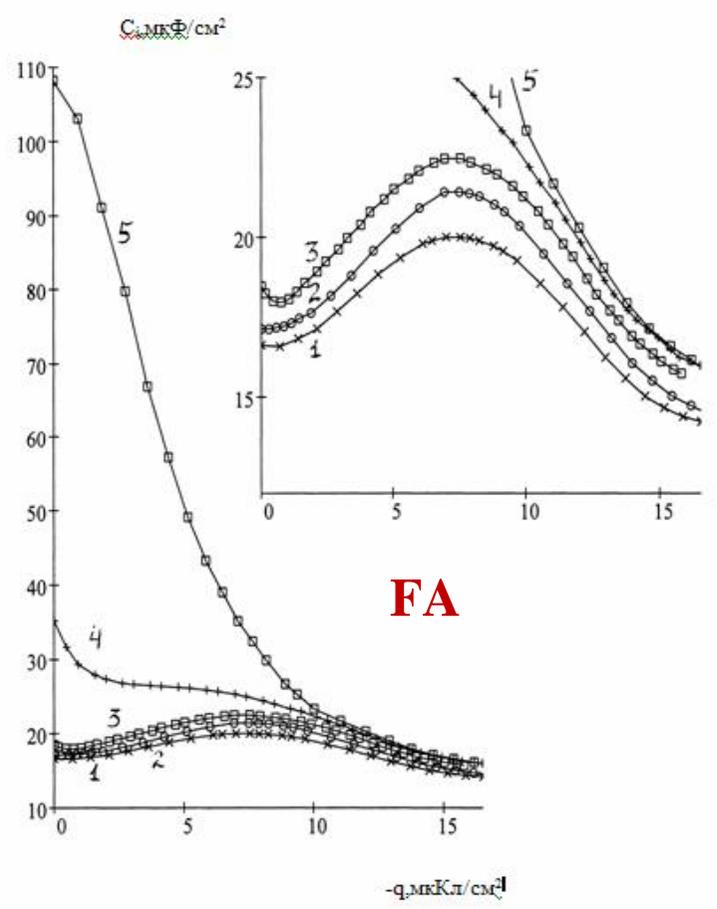
$We,$
 $DN,$

dm-s)



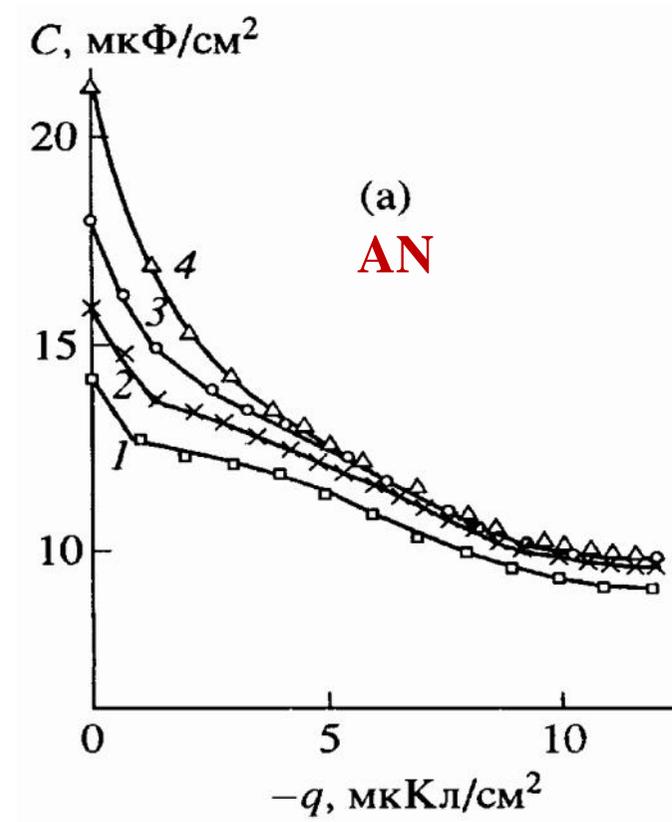
Me H

q_i MeOH : 1 – Hg, 2 – Tl-Ga, 3 – In-Ga, 4 – Cd-Ga, 5 – Ga, 6 – i^{chem} Ga.



FA

q_i F : 1 – Hg, 2 – Pb-Ga, 3 – Tl-Ga, 4 – In-Ga, 5 – Ga.



(a) AN

q_i 0.1 LiClO₄ AN () Hg (1); Tl-Ga (2); In-Ga (3); Ga (4).

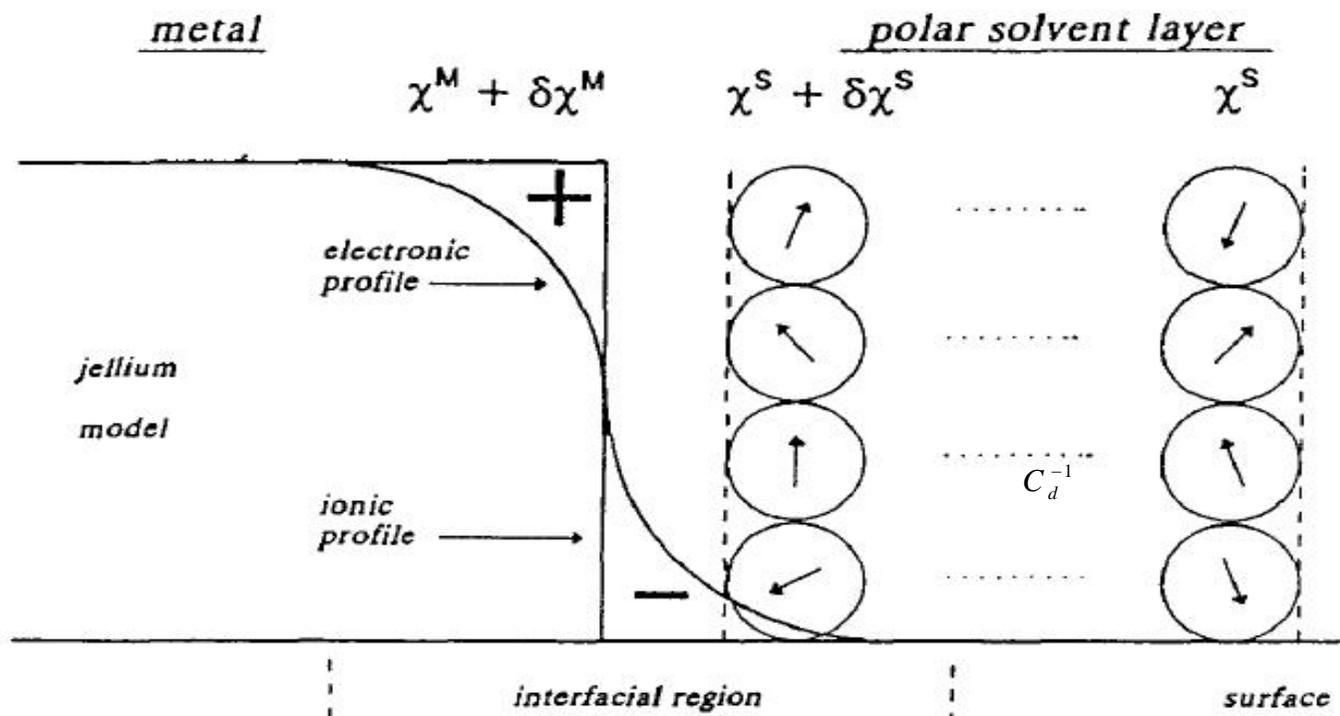


Figure 2. Sketch of an uncharged metal surface (simulated by the jellium model) covered by a macroscopic solvent layer, showing the components of the electric potential drop. $\chi^M + \delta\chi^M$ is the surface potential of the metal modified by the solvent layer; $\chi^S + \delta\chi^S$ is the surface potential of the solvent modified by the contact with the metal; χ^S is the unmodified surface potential of the solvent layer at the external surface.

$$\frac{1}{d_{M-S}} = \frac{1}{d_{M-S}^m} + \frac{1}{d_{M-S}^s}$$

$$\Delta_M^{Hg} C_i^{-1} = \Delta_M^{Hg} C_m^{-1} + \Delta_M^{Hg} C_s^{-1}$$

$$q \ll 0 \quad \Delta_M^{Hg} C_s^{-1} = 0$$

$$\Delta_M^{Hg} d_{M-S} \approx \Delta_M^{Hg} C_m^{-1} = (\Delta_M^{Hg} C_i^{-1})_{q \ll 0}$$

$$\Delta_M^{Hg} d_{M-S}$$

Hg < Tl-Ga In-Ga Ga < Cd-Ga

Hg

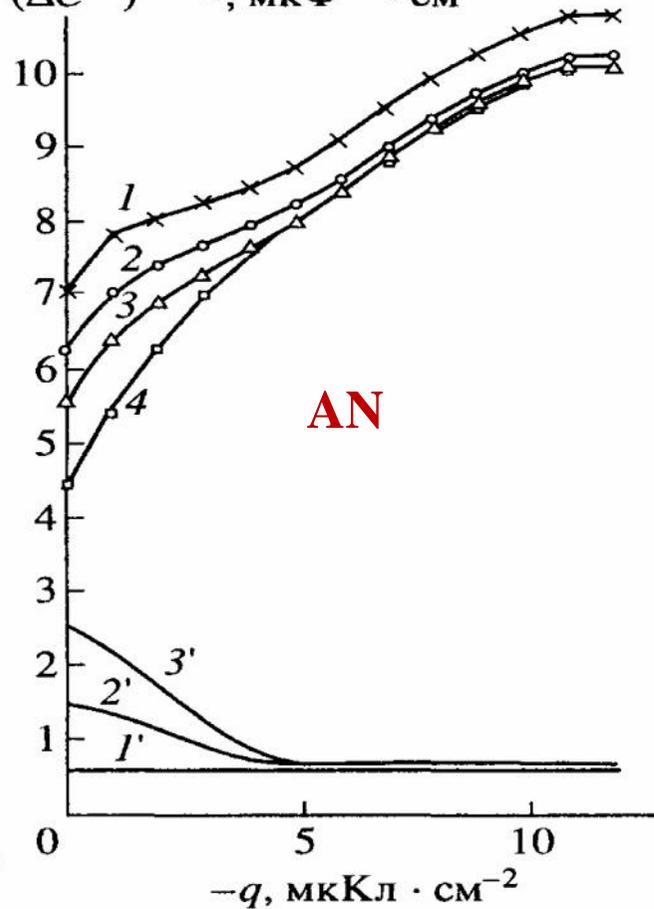
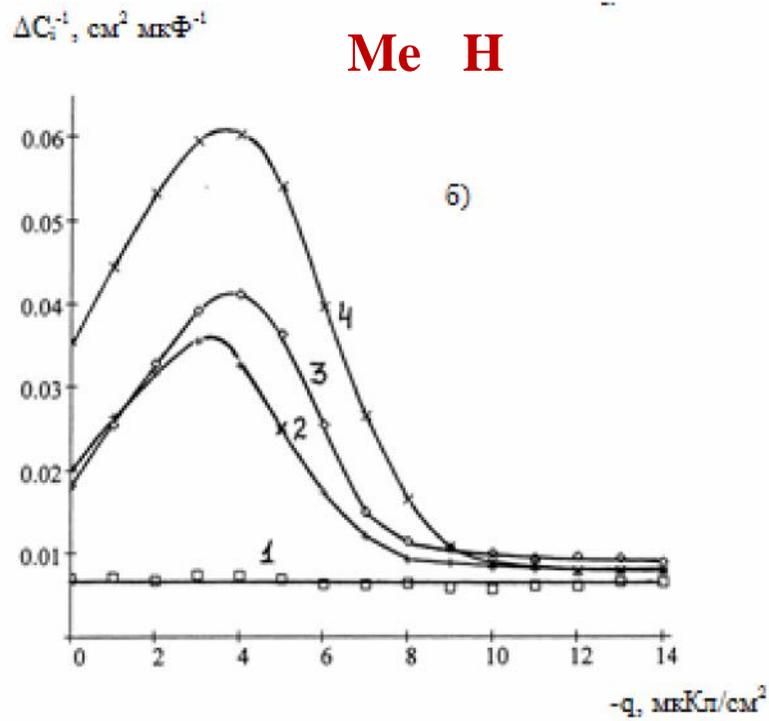
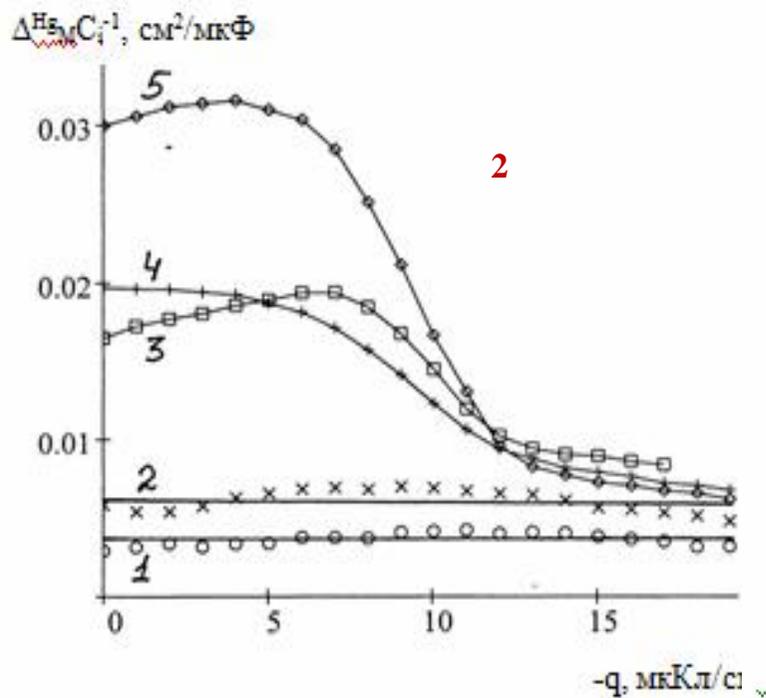
Hg

0.1 -

Hg-

Me H

$C^{-1}, \text{MK}\Phi^{-1} \cdot \text{CM}^2$
 $(\Delta C^{-1})^{\text{M-Hg}}, \text{MK}\Phi^{-1} \cdot \text{CM}^2$

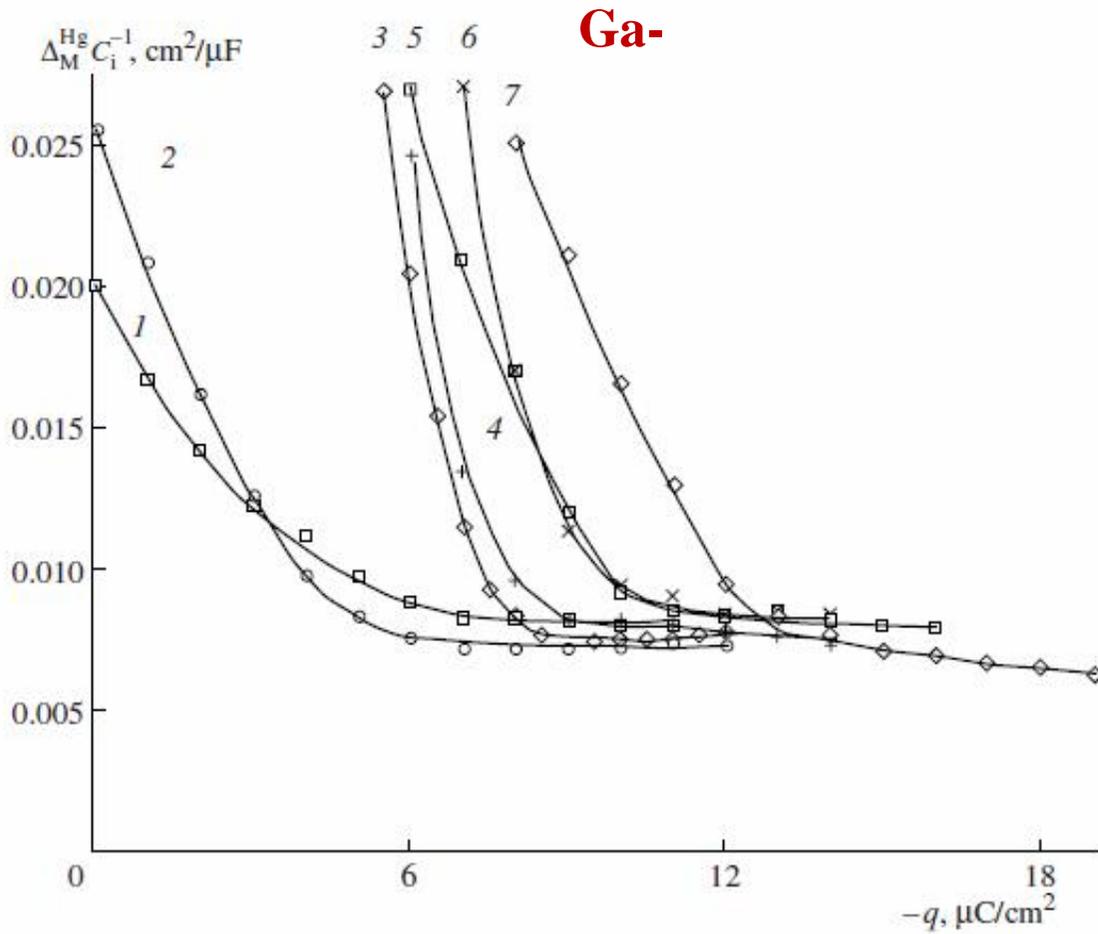


$\Delta_{M_i}^{\text{Hg}} \text{ }^{-1}$

: 1 -

Pb-Ga, 2 - Tl-Ga, 3 - Cd-Ga, 4 - In-Ga, 5 - Ga.

$$(\Delta_{\text{Hg}}^{\text{M}} C_i^{-1})_q$$



$$\Delta_{\text{M}}^{\text{Hg}} C_i^{-1} = (\Delta_{\text{M}}^{\text{Hg}} C_{\text{m}}^{-1} + \Delta_{\text{M}}^{\text{Hg}} C_{\text{s}}^{-1})_{\text{chem}} + (\Delta_{\text{M}}^{\text{Hg}} C_{\text{m}}^{-1})_{\text{phys}}$$

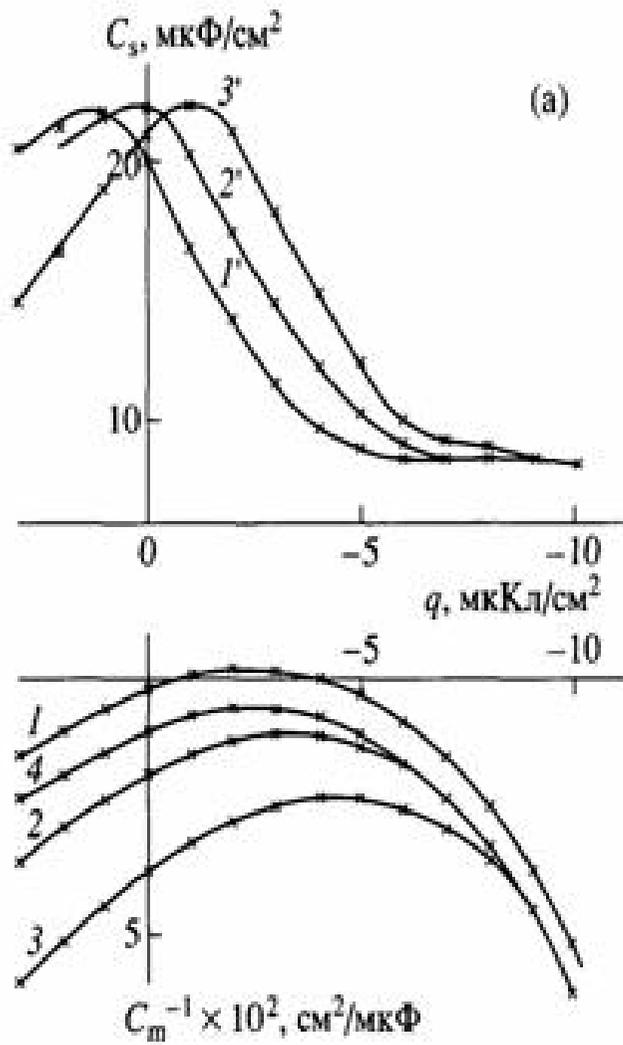
$$q \ll 0 \quad (\Delta_{\text{M}}^{\text{Hg}} C_i^{-1})_{q \ll 0} = (\Delta_{\text{M}}^{\text{Hg}} C_{\text{m}}^{-1})_{\text{phys}}$$

$$(\Delta_{\text{M}}^{\text{Hg}} C_{\text{m}}^{-1})_{\text{phys}}$$

$$\Delta_{\text{M}}^{\text{Hg}} C_i^{-1}$$

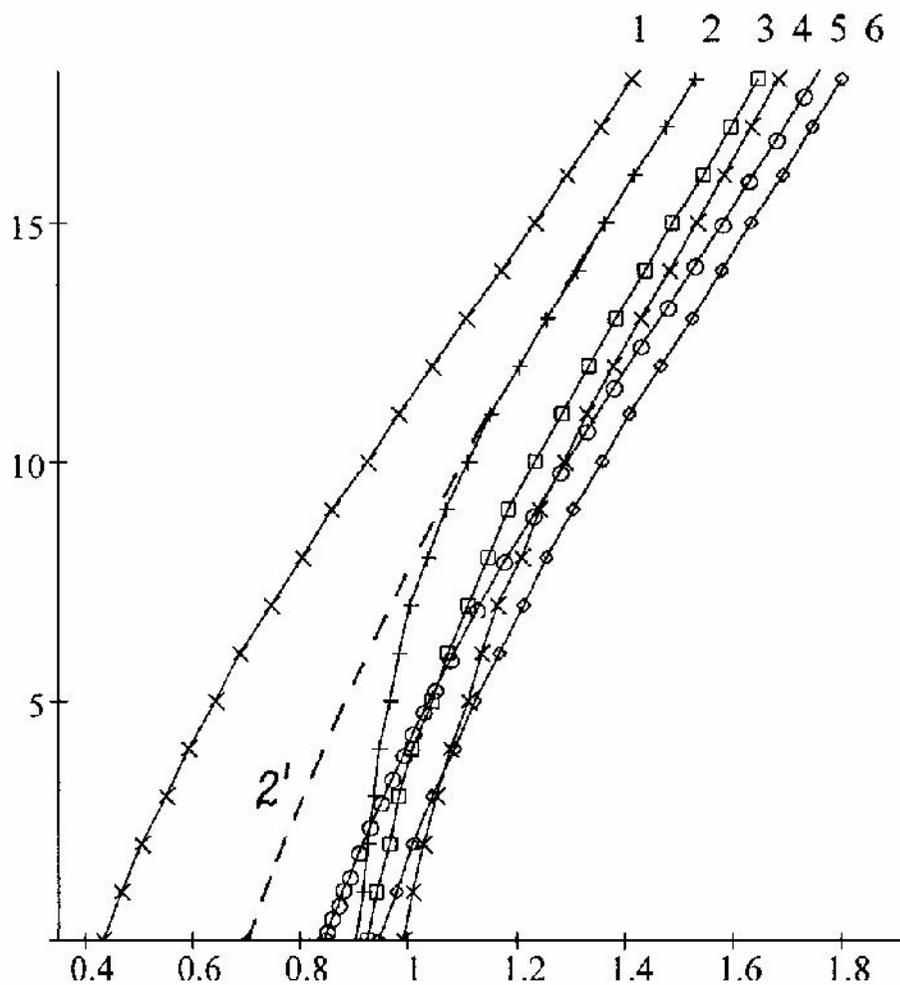
$$(\Delta_{\text{M}}^{\text{Hg}} C_{\text{m}}^{-1} + \Delta_{\text{M}}^{\text{Hg}} C_{\text{s}}^{-1})_{\text{chem}}$$

$$\Delta_{\text{M}}^{\text{Hg}} C_i^{-1}$$



” ” C_m^{-1} C_s
 Hg (1, 1'), Tl-Ga (4, 4'), In-Ga (2, 2') Ga (3, 3').

- $m^{-1}, q-$
 dm-s -
 M-S
 -
 q $C_s, q-$ 2 : 1)
 -
 2)
 -
 dm-s $m^{-1}, q-$



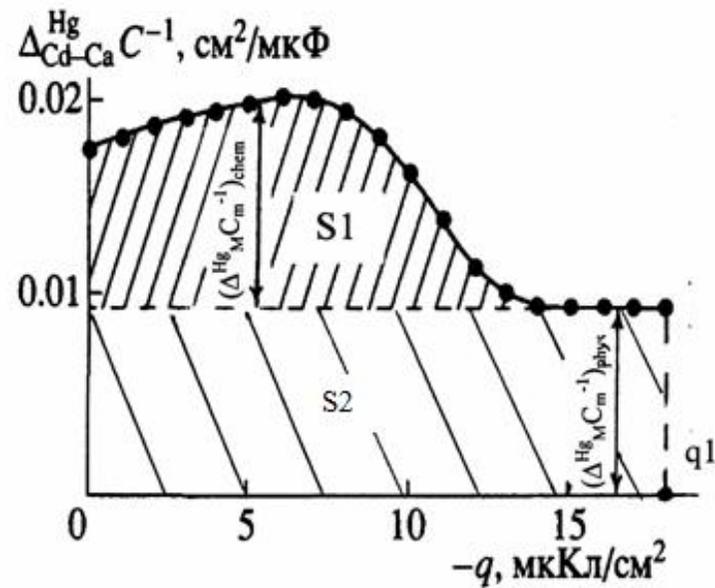
$q \ 0.5$

Na_2SO_4 : 1 – Ga, 2 – In–Ga, 3 – Cd–Ga,
 4 – Tl–Ga, 5 – Tl–Ga, 6 – Hg; C^{chem}, q -
 1'–Ga, 2'–In–Ga.

q, E -

$$(\Delta_M^{\text{Hg}} E_{\text{chem}})_{q=0} = \Delta_M^{\text{Hg}} E_{q=0} - \Delta_M^{\text{Hg}} E_{q1} - q_1 (\Delta_M^{\text{Hg}} C_m^{-1})_{\text{phys}}$$

$$(\Delta_M^{\text{Hg}} E_{\text{chem}})_{\alpha=0} = \Delta_M^{\text{Hg}} E_{\alpha=0} - (\Delta_M^{\text{Hg}} W_e / e_0)_{\text{el}}$$



$\Delta_M^{\text{Hg}} C_i^{-1}$ Cd–Ga

Ga-, In-Ga-, Cd-Ga-, Tl-Ga-, Bi-Ga-, Sn-Ga- Pb-Ga - Hg-

Металл	Растворитель	$\Delta_{M}^{H_2} E_{q=0}$, В	$(\Delta_{M}^{H_2} E_{chem}^{-1})_{p=0}$, см ² /мксФ	$(\Delta_{M}^{H_2} W/c_2)_{p=0}$, В	$(\Delta_{M}^{H_2} E_{chem})_{p=0}$, В _{chem}
Ga	AN	0.3	0.007	0.23	0.03
	PC	0.3	0.008	0.24	0.06
	H ₂ O	0.5	0.007	0.24	0.26
	FA	0.56	0.007	0.25	0.31
	MeOH	0.56	0.008	0.25	0.31
	EtOH	0.57	0.008	0.25	0.32
	N-MF	0.59	0.006	0.24	0.33
	DMF	0.64	-	-	0.40
	DMSO	0.72	-	-	0.47
	HMPTA	0.90	-	-	0.66
EDA	1.04	-	-	0.8	
In-Ga	AN	0.42	0.007	0.39	0.03
	PC	0.43	0.008	0.40	0.03
	H ₂ O	0.48	0.0075	0.39	0.09
	FA	0.49	0.0075	0.39	0.10
	MeOH	0.53	0.008	0.39	0.14
	EtOH	0.54	0.008	0.39	0.13
	N-MF	0.55	0.006	0.39	0.16
	DMF	0.59	-	-	0.20
	DMSO	0.63	-	-	0.24
	HMPTA	0.80	-	-	0.41
EDA	0.98	-	-	0.58	

Металл	Растворитель	$\Delta_{M}^{H_2} E_{q=0}$, В	$(\Delta_{M}^{H_2} E_{chem}^{-1})_{p=0}$, см ² /мксФ	$(\Delta_{M}^{H_2} W/c_2)_{p=0}$, В	$(\Delta_{M}^{H_2} E_{chem})_{p=0}$, В _{chem}
Tl-Ga	AN	0.31	0.006	0.32	0
	PC	0.33	0.0063	0.33	0
	H ₂ O	0.32	0.006	0.32	0
	FA	0.33	0.06	0.33	0
	MeOH	0.33	0.007	0.33	0
	EtOH	0.33	0.0063	0.32	0
	N-MF	0.36	0.0033	0.33	0.03
	DMF	0.38	-	-	0.03
	DMSO	0.39	-	-	0.07
	HMPTA	0.7	-	-	0.17
Cd-Ga	AN	0.31	0.09	0.48	0.3
	PC	0.31	0.0083	0.47	0.04
	GBL	0.33	0.09	0.47	0.08
	H ₂ O	0.36	0.009	0.45	0.11
	MeOH	0.65	0.009	0.47	0.18
	DMF	0.67	-	-	0.20
	DMSO	0.70	-	-	0.23
	HMPTA	0.92	-	-	0.46
EDA	1.06	-	-	0.60	
Bi-Ga	AN	0.183	0.002	0.18	0
	H ₂ O	-	0.0025	0.19	0
Sn-Ga	AN	0.17	0.004	0.17	0
	H ₂ O	-	0.0045	0.17	0.03
Pb-Ga	PC	0.42	0.003	0.42	0
	H ₂ O	0.42	0.0035	0.42	0
	FA	0.42	0.003	0.42	0

$$E_{q=0} = We/e_0 + (E_{\text{Chem}})_{q=0} + \text{const}, \quad E_{\text{Chem}} = f(We, DN, d)$$

sp-

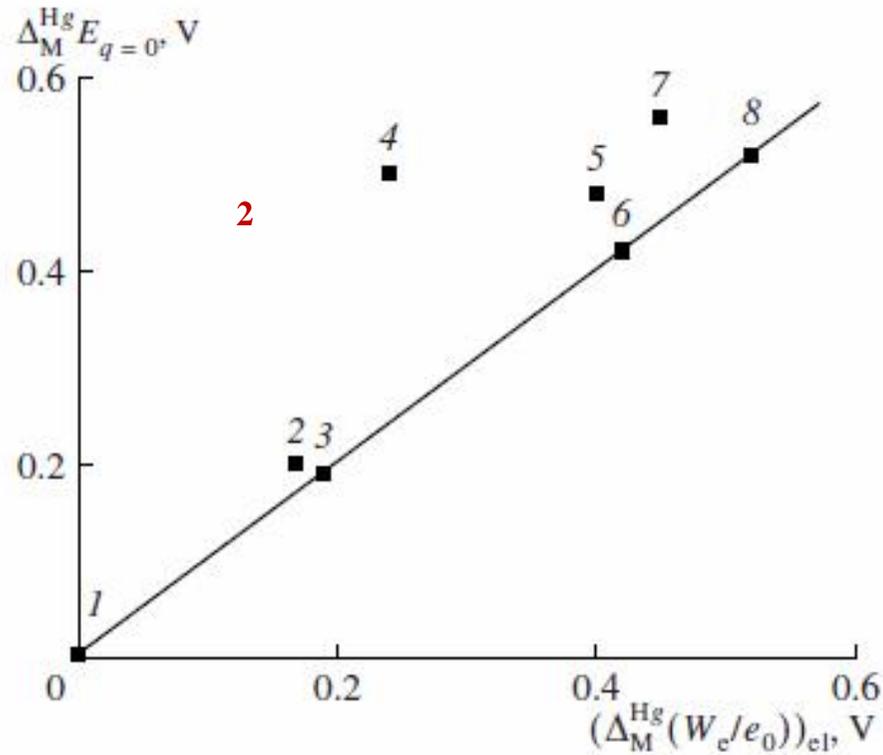


Fig. 4. Dependence of $\Delta_M^{\text{Hg}} E_{q=0}$ on $((\Delta_M^{\text{Hg}} W_e/e_0)_{\text{el}})$ in aqueous solutions of surface-inactive electrolyte at different electrodes: (1) Hg, (2) Sn, (3) Bi, (4) Ga, (5) In-Ga, (6) Pb-Ga, (7) Cd-Ga, (8) Tl-Ga.

Hg -

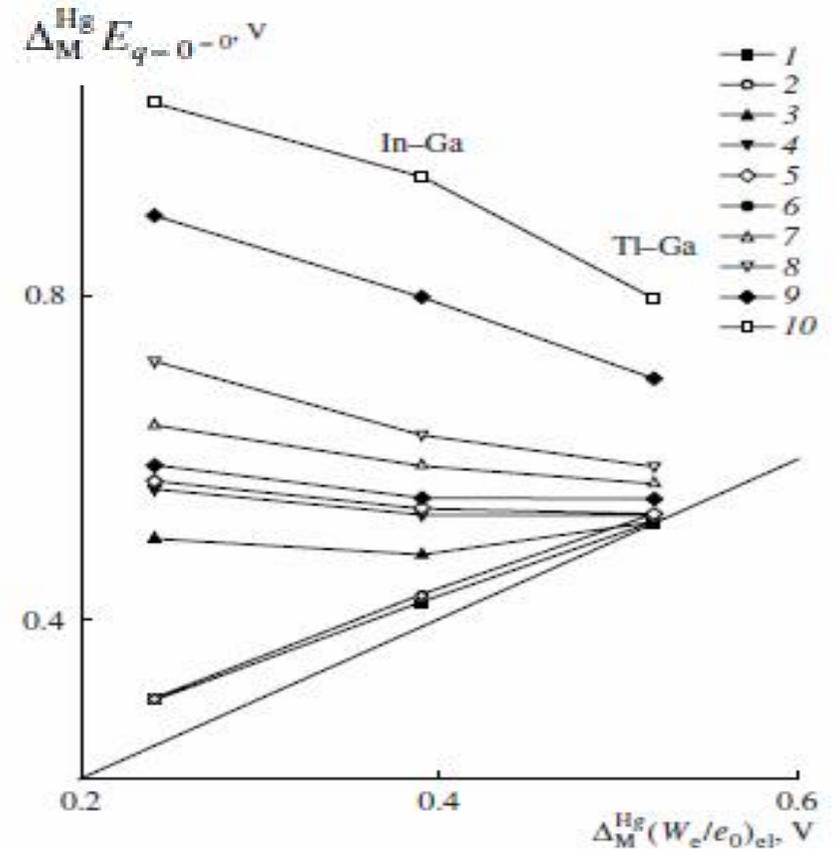
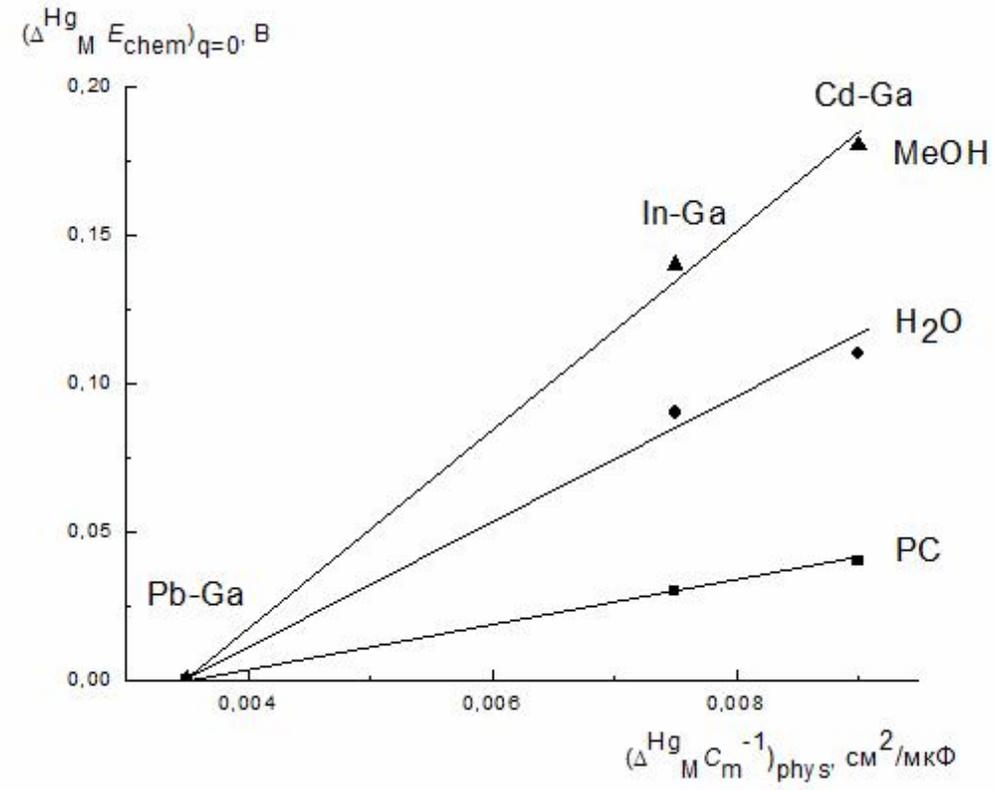
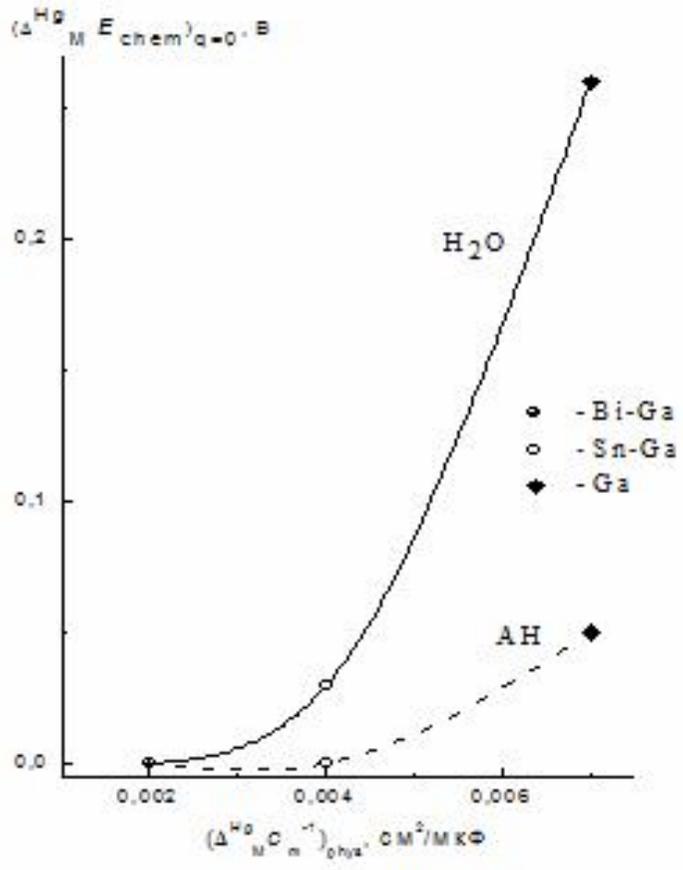


Fig. 7. Relations between $\Delta_M^{\text{Hg}} E_{q=0}$ and electrochemical work function $((\Delta_M^{\text{Hg}} W_e/e_0)_{\text{el}})$ for Ga-, In-Ga-, and Tl-Ga-electrodes in different solvents: (1) AN, (2) PC, (3) H₂O, (4) MeOH, (5) EtOH, (6), N-MF, (7) DMF, (8) DMSO; (9) HMPA, (10) EDA.

We/e_0



Sn-Ga Ga- : $(\Delta_M^{Hg} C_m^{-1})_{phys} \cdot$ Bi-Ga, -
 : AN 2 .

In-Ga- Cd-Ga- : $(\Delta_M^{Hg} C_m^{-1})_{phys} \cdot$ Pb-Ga-,
 : MeOH, 2 PC.

We/e_0
 dm-s,

DN

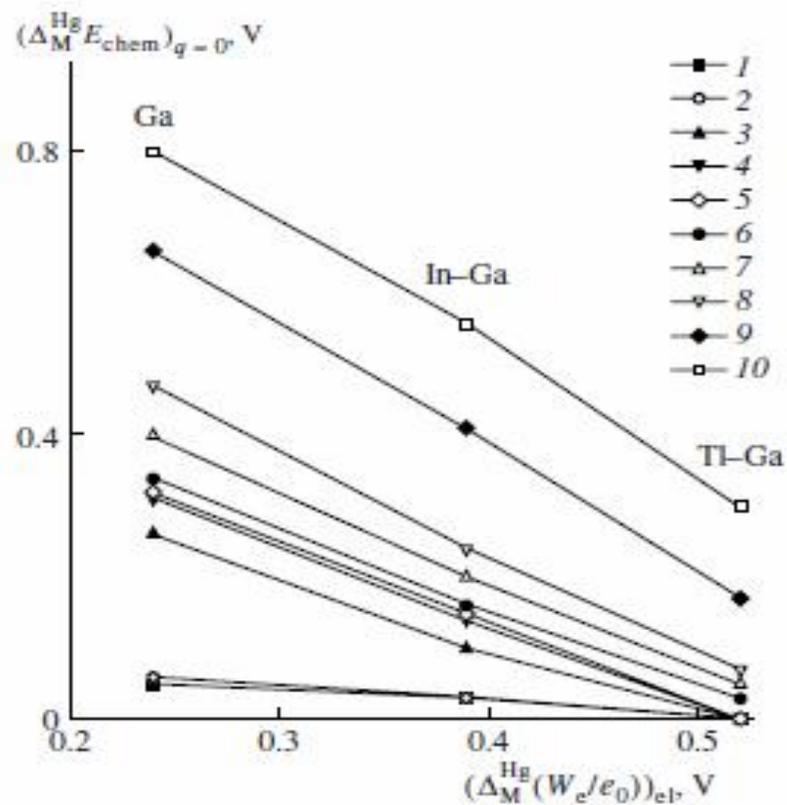


Fig. 6. Relations between the solvent's chemisorption potential drop $(\Delta_M^{\text{Hg}} E_{\text{chem}})_{q=0}$ and electrochemical work function $(\Delta_M^{\text{Hg}} W_e/e_0)_{\text{el}}$ for Ga-, In-Ga-, and Tl-Ga-electrodes in different solvents: (1) AN, (2) PC, (3) H₂O, (4) MeOH, (5) EtOH, (6) N-MF, (7) DMF, (8) DMSO; (9) HMPA, (10) EDA.

dm-s

(Tl-Ga) < (In-Ga) <

Ga

(. .

)

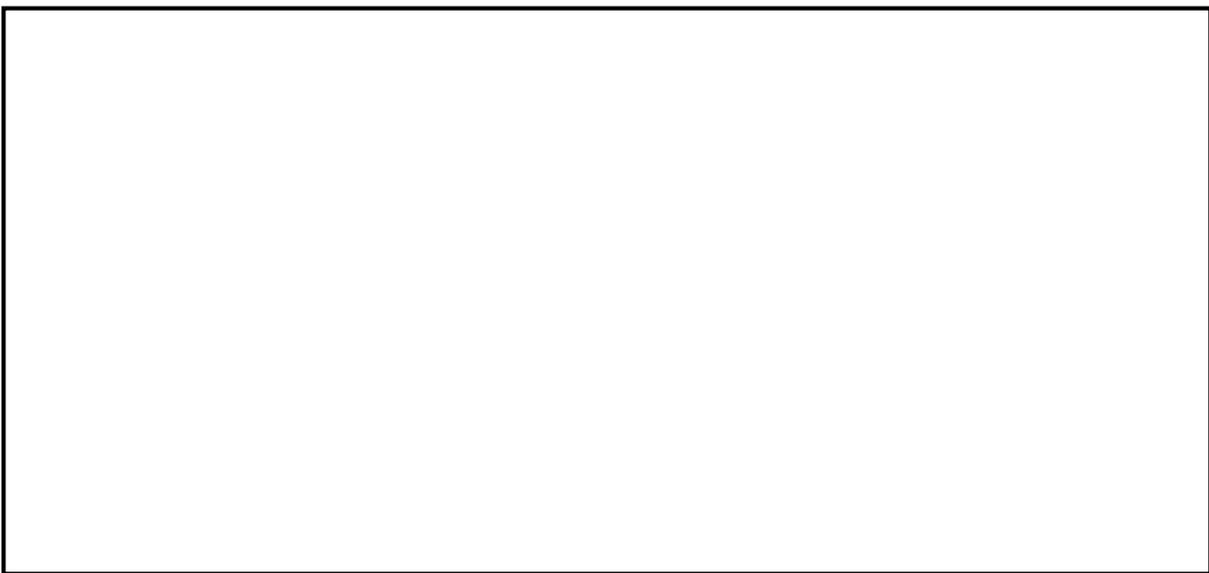
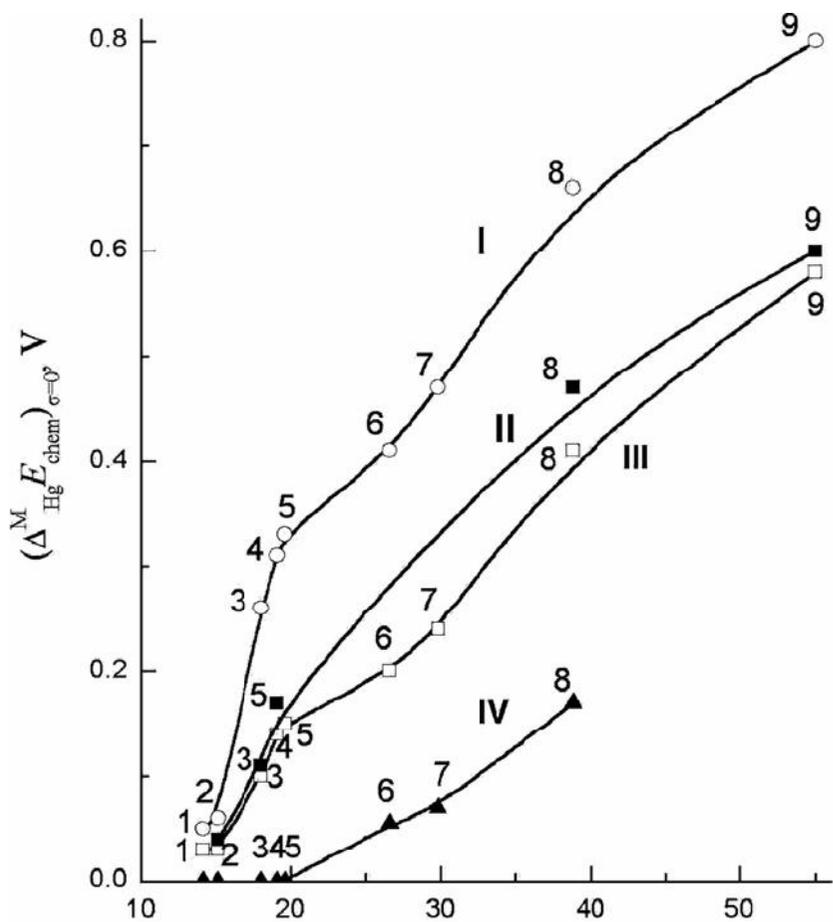
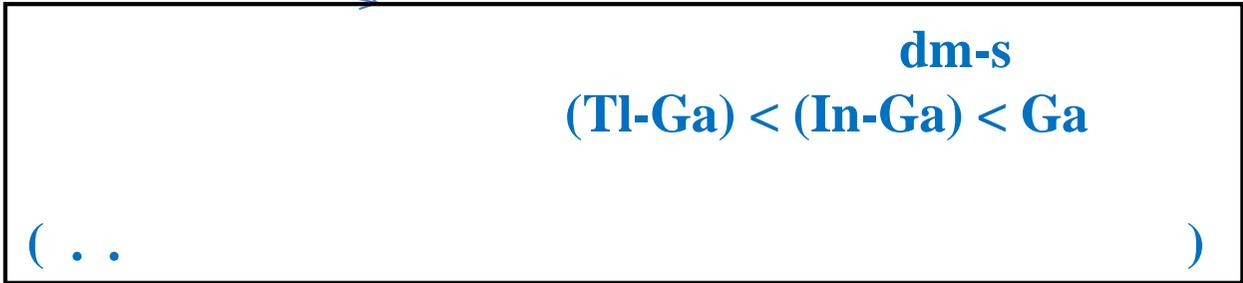
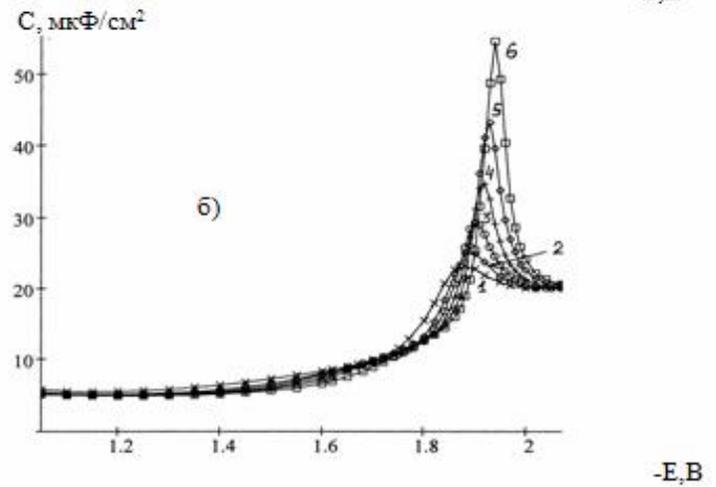
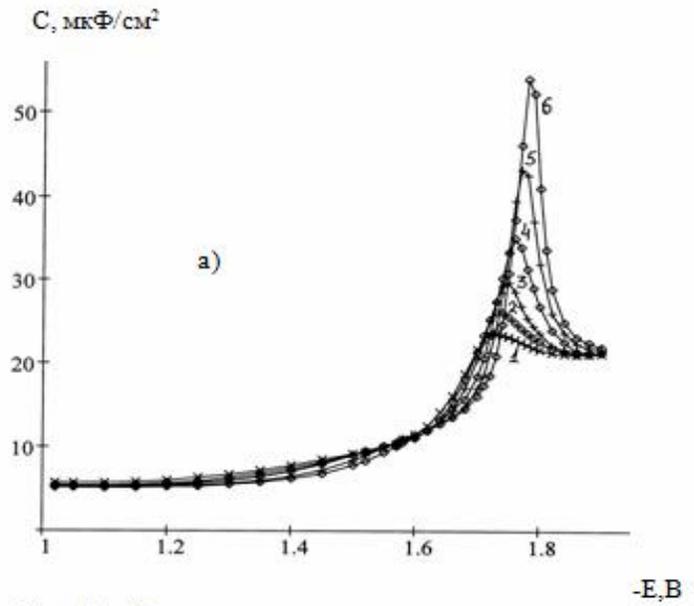


Fig. 16. The dependence of chemisorption potential drop $(\Delta_M^{\text{Hg}} E_{\text{chem}})_{\sigma=0}$ on solvent donor numbers DN for Ga (I), Cd-Ga (II), In-Ga (III) and Tl-Ga (IV). The figures specify the following solvents: (1) AN, (2) PC, (3) water, (4) MeOH, (5) EtOH, (6) DMF, (7) DMSO, (8) HMPTA, (9) EDA.





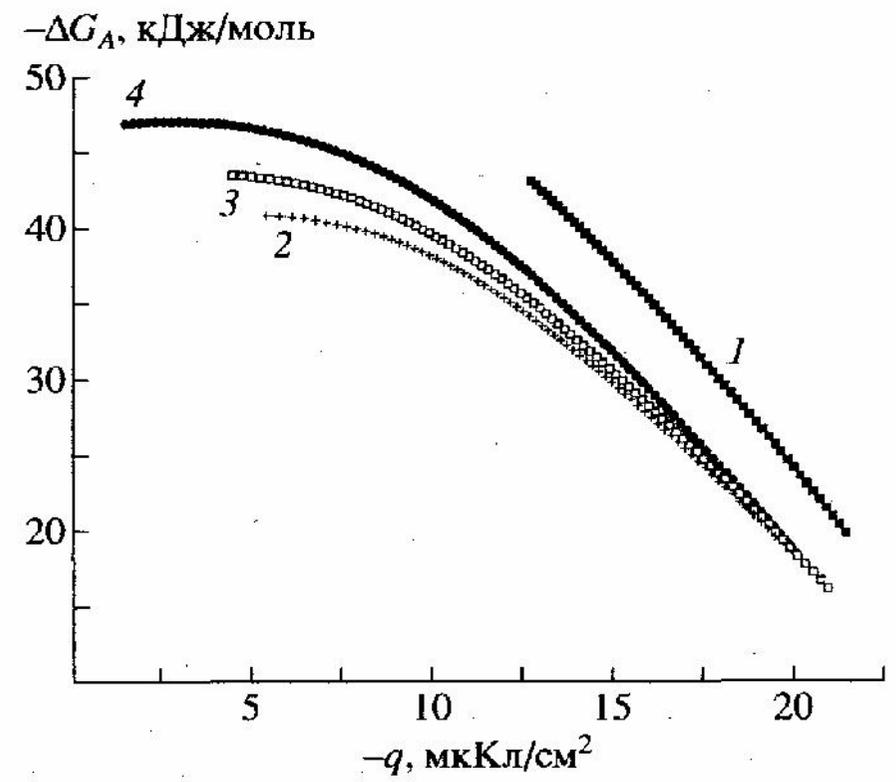
0,05

Hg

dms,

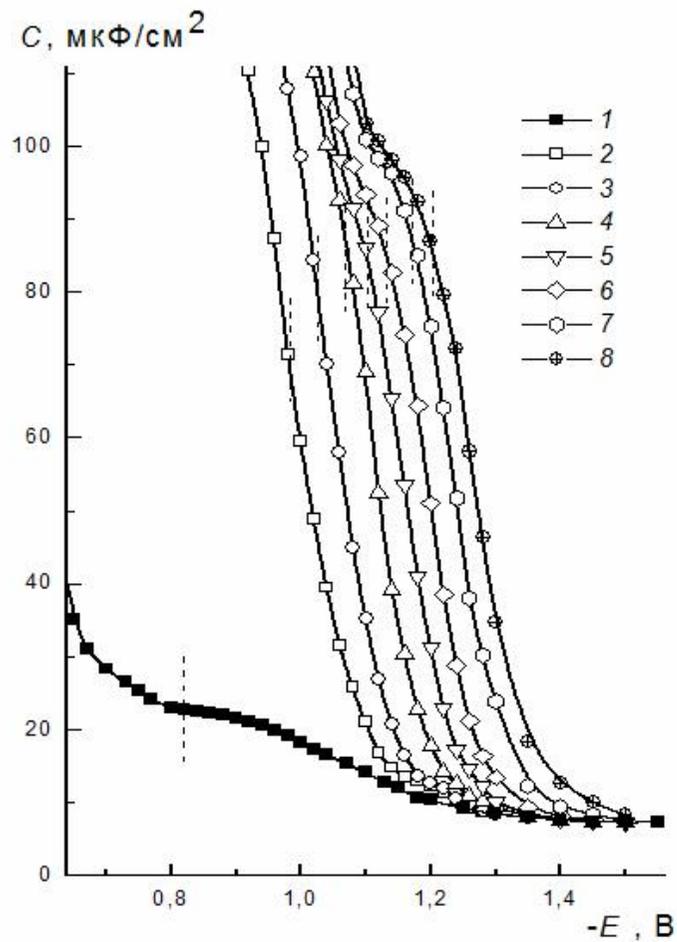
$q=0,$

$q \ll 0,$



2- $2.5 \cdot 10^{-4}$; 3- $3.5 \cdot 10^{-4}$; 4- $5 \cdot 10^{-4}$; 5- $7.08 \cdot 10^{-4}$; 6- 10^{-3} , In-Ga
 () Tl-Ga ().

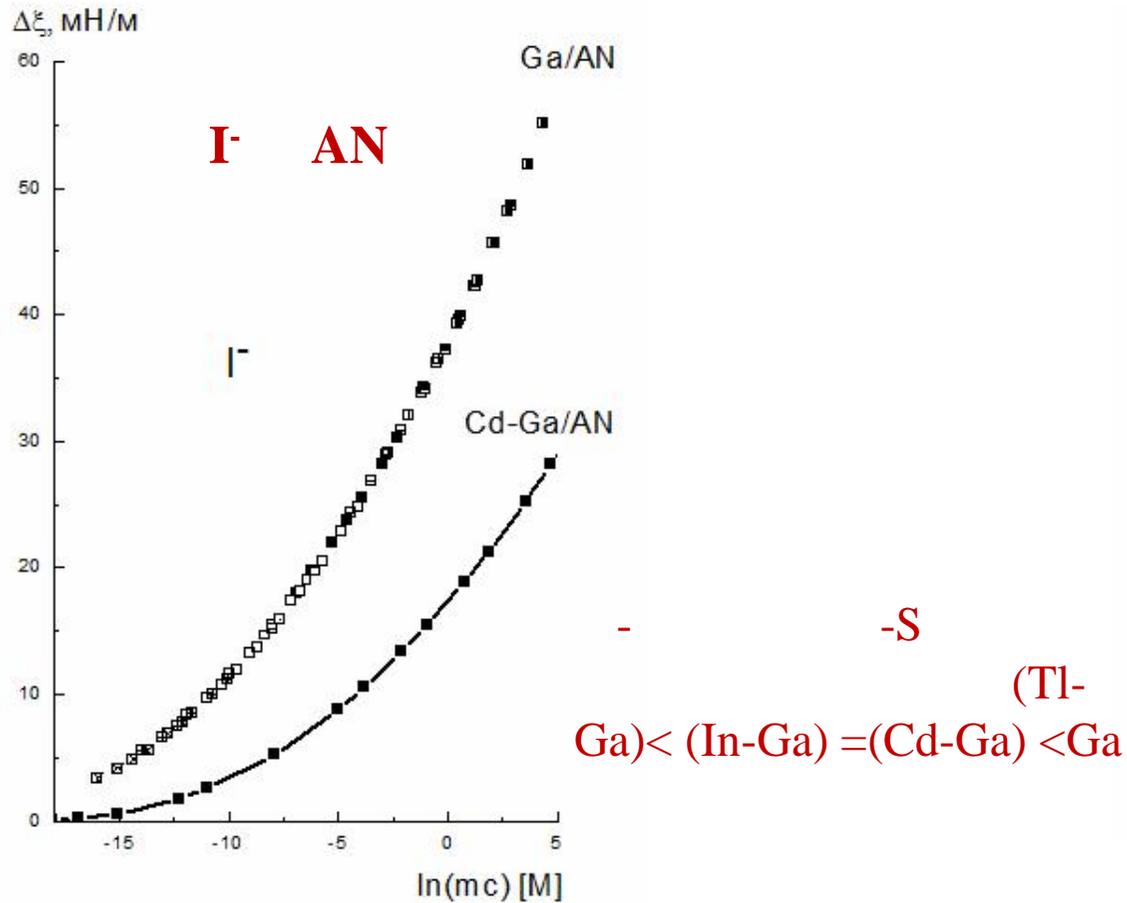
0.05 Na_2SO_4 : 1 - Hg, 2 - Ga, 3 - In-Ga 4 - Tl-Ga.



Кривые дифференциальной емкости для системы (Cd-Ga) / [ДМФ + 0.1*m* M LiCl + 0.1(1-*m*) M LiBF₄] при следующих значениях *m*: 1 – 0; 2 – 0.01; 3 – 0.02; 4 – 0.05; 5 – 0.1; 6 – 0.2; 7 – 0.5; 8 – 1. Вертикальные пунктирные линии соответствуют E_j .

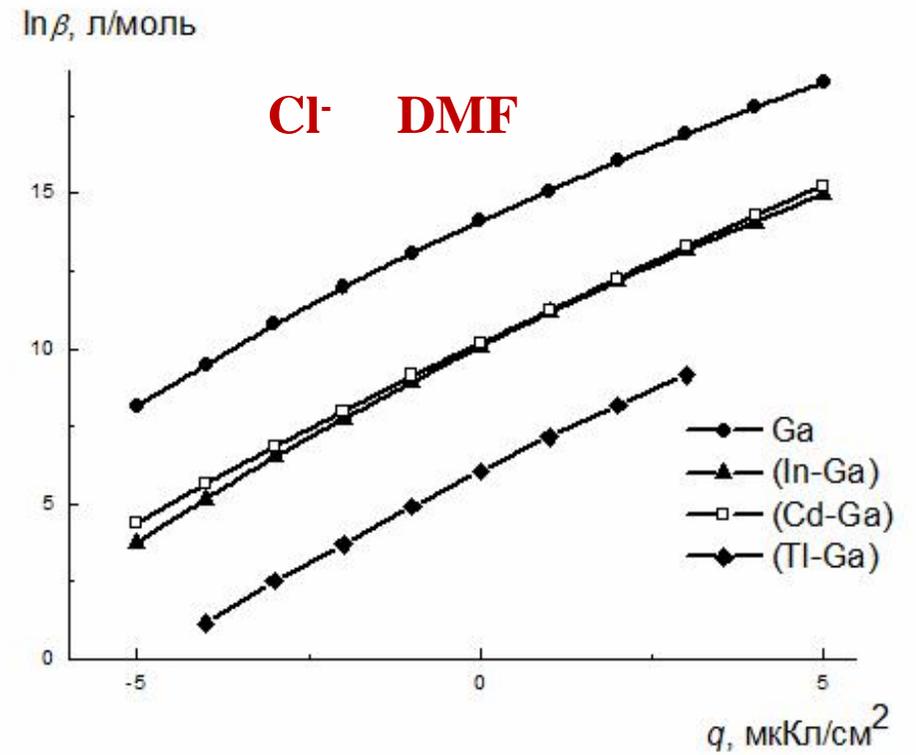
$$\ln \frac{G}{G_0} + \ln(mc) = -2a$$

$$G = RT \ln \dots$$



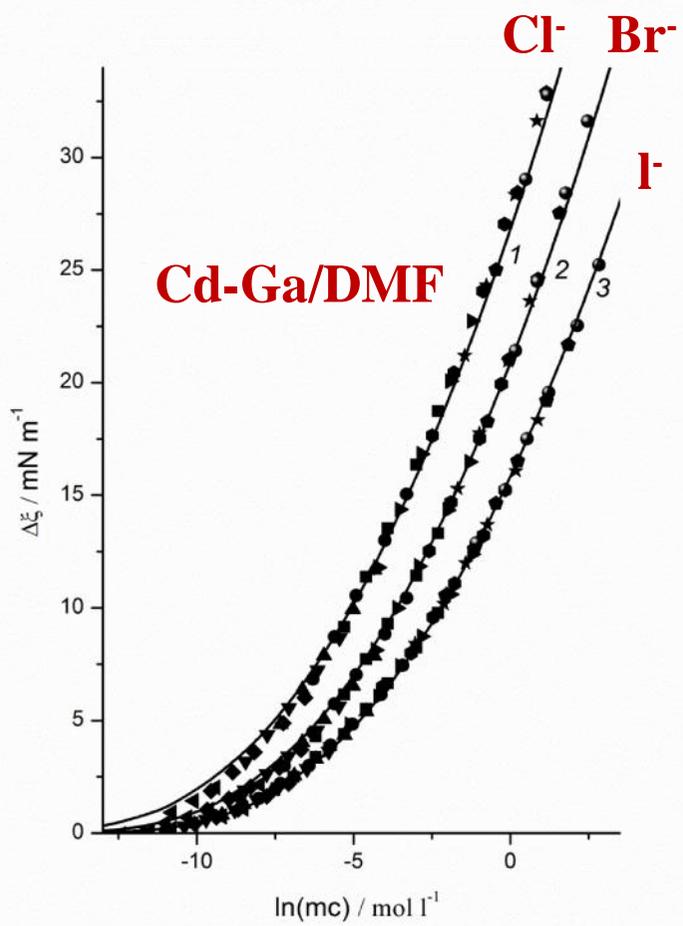
Ga/AN Cd-Ga/AN,
 $\ln(mc),$

$m \quad 0.01 \quad 1$



$\ln q:$

Ga/[M + 0.1m LiCl + 0.1(1-m) LiClO₄],
 (Cd-Ga)/[M + 0.1m LiCl + 0.1(1-m) LiBF₄],
 (In-Ga)/[M + 0.1m LiCl + 0.1(1-m) LiClO₄],
 (Tl-Ga)/[M + 0.1m LiCl + 0.1(1-m) LiClO₄]



1- Cl⁻, 2- Br⁻, 3- I⁻ s

Cd-Ga/DMF,
ln(mc),

m 0.01

G_{M-S} , G_{M-} ,
 Ga, (In-Ga) (Cd-Ga) , G_{M-S} ,
 G_{M-} ,
 I⁻ < Br⁻ < Cl⁻ .
 G_{M-} ,
 I⁻ < Br⁻ < Cl⁻ ,
 G_{M-} ,
 M-S (Hg, Bi) ,
 Cl⁻ < Br⁻ ,
 < I⁻ ,

2018-2019

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